Product data sheet

1. General description

Planar passivated sensitive gate four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in general purpose bidirectional switching and phase control applications. This sensitive gate "series E" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate
- Triggering in all four quadrants

3. Applications

- General purpose motor control
- General purpose switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage			-	-	600	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 20 \text{ms}$; Fig. 4; Fig. 5		-	-	95	A
T _j	junction temperature			-	-	125	°C
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 99 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3		-	-	12	А
Static charac	teristics		1			'	
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$		-	2.5	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{ G-;}$ $T_j = 25 \text{ °C; } Fig. 7$		-	4	10	mA





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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 7}}{}$		-	5	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 7$		-	11	25	mA
Dynamic characteristics							
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; $(V_{DM}$ = 67% of V_{DRM}); exponential waveform; gate open circuit		-	150	-	V/µs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2
2	T2	main terminal 2	7 7	Sym051
3	G	gate		
mb	Т2	mounting base; main terminal 2		
			TO-220AB (SOT78)	

6. Ordering information

Table 3. Ordering information

Table 6. Grading information						
Type number	Package					
	Name	Description	Version			
BT138-600E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			
BT138-600E/DG	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

7. Marking

Table 4. Marking codes

Type number	Marking code
BT138-600E	
BT138-600E/DG	BT138-600EDG

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 99 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	12	А
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 20 \text{ms}$; Fig. 4; Fig. 5	-	95	А
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	-	105	А
I ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	45	A ² s
dl _T /dt	rate of rise of on-state current	I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2+ G+	-	50	A/µs
		I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2+ G-	-	50	A/µs
		I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2- G-	-	50	A/µs
		I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2- G+	-	10	A/µs
I _{GM}	peak gate current		-	2	Α
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C

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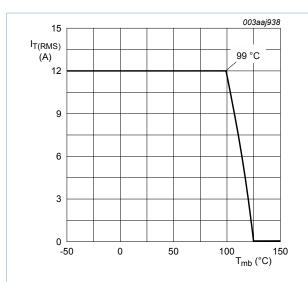
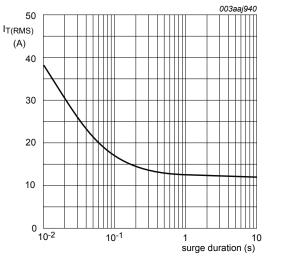
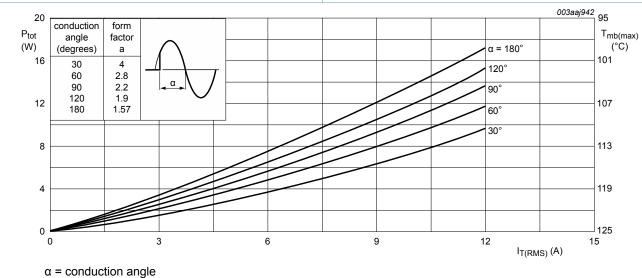


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



f = 50 Hz; $T_{mb} = 99 \text{ }^{\circ}\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values



a = form factor = $I_{T(RMS)} / I_{T(AV)}$

Total power dissipation as a function of RMS on-state current; maximum values Fig. 3.

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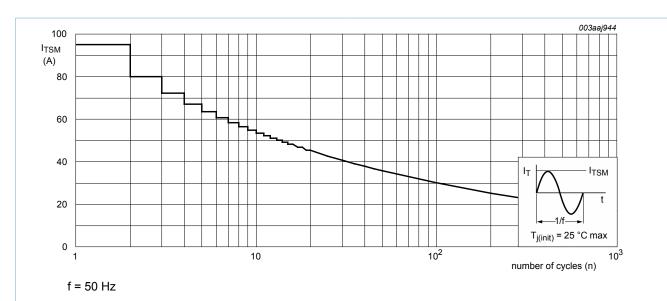


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

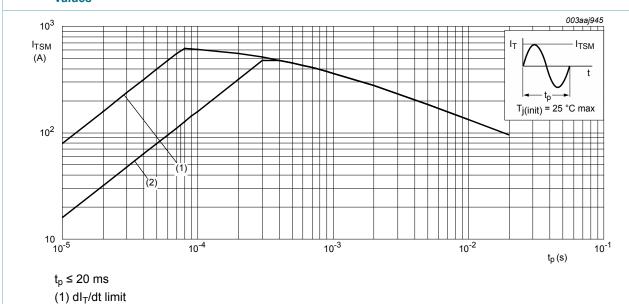


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

(2) T2- G+ quadrant limit

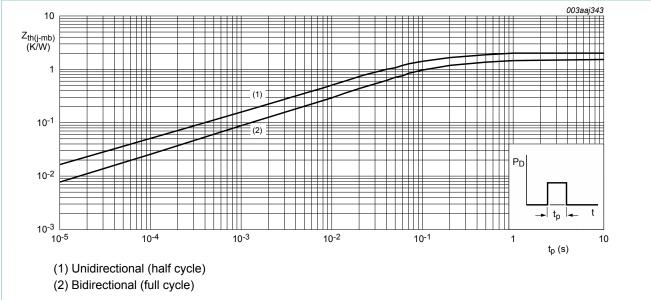
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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance	full cycle; Fig. 6	-	-	1.5	K/W
	from junction to mounting base	half cycle; Fig. 6	-	-	2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W



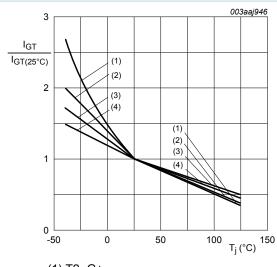
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		'		'	
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	-	2.5	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	4	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2- \text{ G-;}$ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$	-	5	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 7}$	-	11	25	mA
L	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 8</u>	-	-	30	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 8</u>	-	-	40	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	-	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	-	40	mA
Н	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	30	mA
/ _T	on-state voltage	I _T = 15 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.4	1.65	V
/ _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.25	0.4	-	V
D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic c	haracteristics		l	1	1	
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 402 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	-	150	-	V/µs
gt	gate-controlled turn-on time	I_{TM} = 16 A; V_D = 600 V; I_G = 0.1 A; $dI_G/$ dt = 5 A/ μ s	-	2	-	μs

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- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

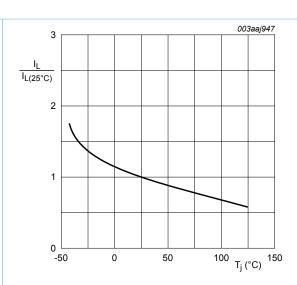
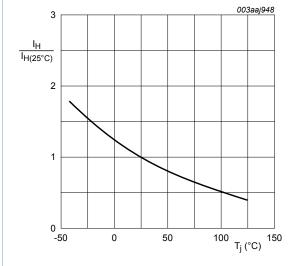
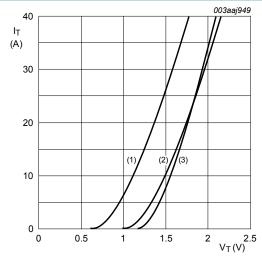


Fig. 8. Normalized latching current as a function of junction temperature



Normalized holding current as a function of junction temperature



 $V_o = 1.175 \text{ V}; R_s = 0.0316 \Omega$

- (1) T_i = 125 °C; typical values
- (2) T_i = 125 °C; maximum values
- (3) T_i = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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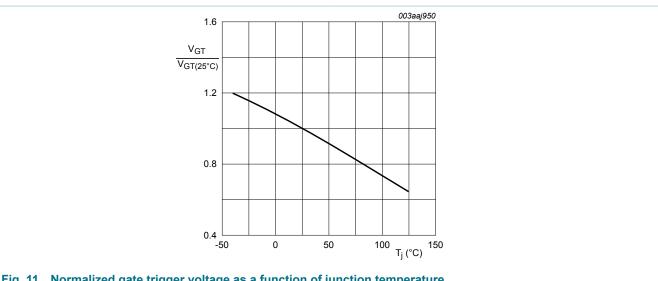
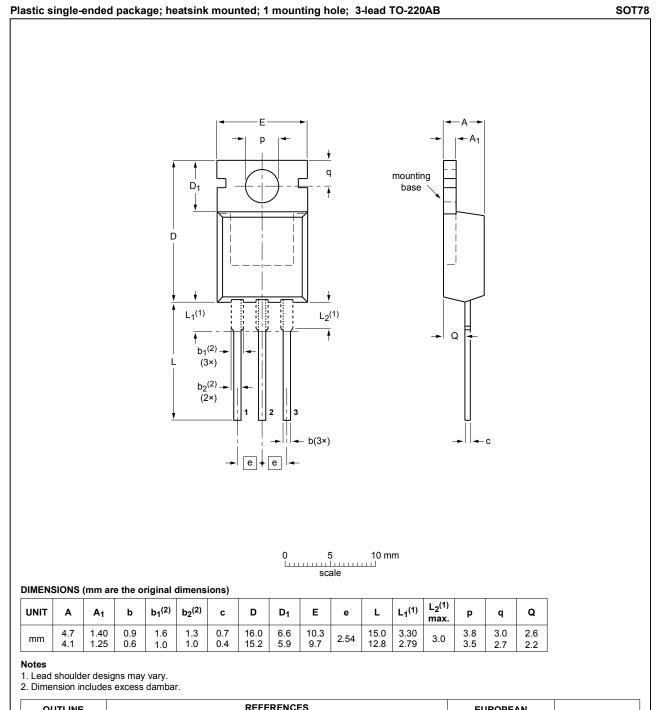


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

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11. Package outline



OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT78		3-lead TO-220AB	SC-46	\bigoplus	08-04-23 08-06-13	

Fig. 12. Package outline TO-220AB (SOT78)

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